TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

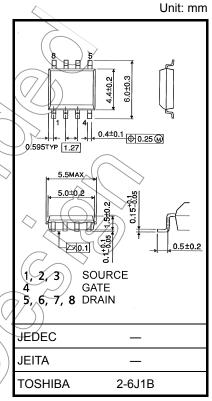
# **TPC8040-H**

High Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: QSW = 5.1 nC (typ.)
- Low drain-source ON-resistance: RDS (ON) =  $6.4 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 48 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = 10 \mu A (max) (V_{DS} = 30 V)$
- Enhancement mode:  $V_{th} = 1.3$  to 2.3 V ( $V_{DS} = 10$  V,  $I_{D} = 0.2$  mA)

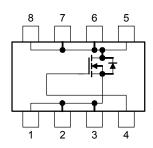
### Absolute Maximum Ratings (Ta = 25°C)

| Characteristic                                       |                 | Symbol            | Rating     | Unit       |
|--|-----------------|-------------------|------------|------------|
| Drain-source voltage                                 |                 | $V_{DSS}$         | 30         | V          |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) |                 | V <sub>DGR</sub>  | 30         | V          |
| Gate-source voltage                                  |                 | V <sub>GSS</sub>  | ±20        | < <u>\</u> |
| Drain current  | DC (Note 1)     | ID( (             | 13         | A          |
|  | Pulsed (Note 1) | DEP.              | 52         | , ^        |
| Drain power dissipation (t = 10 s)<br>(Note 2a)      |                 | PD                | 1.9        | /w         |
| Drain power dissipation (t = 10 s) (Note 2b)         |                 | D                 | 1.0        | ∑w         |
| Single pulse avalanche energy (Note 3)               |                 | EAS               | 110        | mJ         |
| Avalanche current                                    |                 | IAR               | 13         | Α          |
| Repetitive avalanche energy (Note 2a) (Note 4)       |                 | EAR               | 2.0        | mJ         |
| Channel temperature                                  |                 | ₹ <sup>T</sup> ch | 150        | °C         |
| Storage temperature range                            |                 | T <sub>stg</sub>  | -55 to 150 | °C         |
|  | / />            |                   |            |            |



Weight: 0.085 g (typ.)

### **Circuit Configuration**



Note: For Notes 1 to 4, refer to the next page.

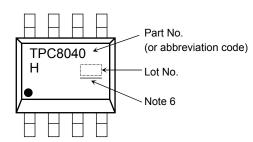
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating" Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

#### **Thermal Characteristics**

| Characteristic  | Symbol                 | Max  | Unit |
|---|------------------------|------|------|
| Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)   | R <sub>th (ch-a)</sub> | 65.8 | °C/W |
| Thermal resistance, channel to ambient $(t=10 \; s) \eqno (Note \; 2b)$ | R <sub>th (ch-a)</sub> | 125  | °C/W |

#### Marking (Note 5)



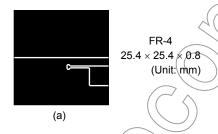
Note 6: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

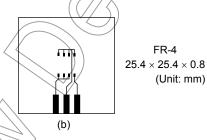
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Note 1: Ensure that the channel temperature does not exceed 150°C

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3:  $V_{DD} = 24 \text{ V}$ ,  $T_{Ch} = 25^{\circ}\text{C}$  (initial),  $L = 500 \mu\text{H}$ ,  $R_G = 25 \Omega$ ,  $L_{AR} = 13 \text{ A}$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1:

\* Weekly code: (Three digits)

Week of manufacture

(0) for the first week of the year: sequential number up to 52 or 53)

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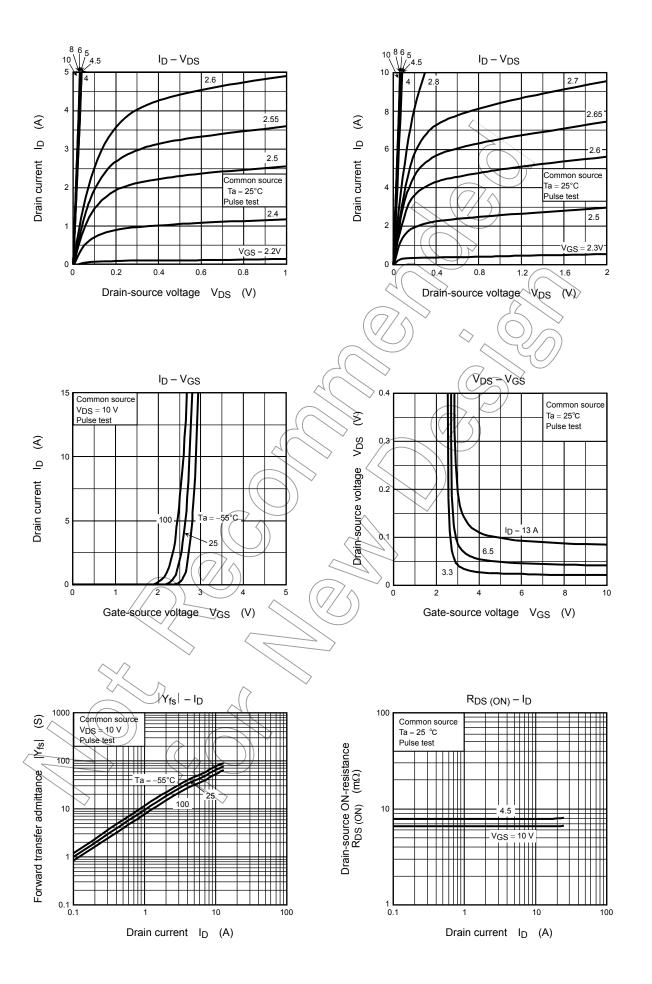
Year of manufacture (The last digit of the year)

## **Electrical Characteristics (Ta = 25°C)**

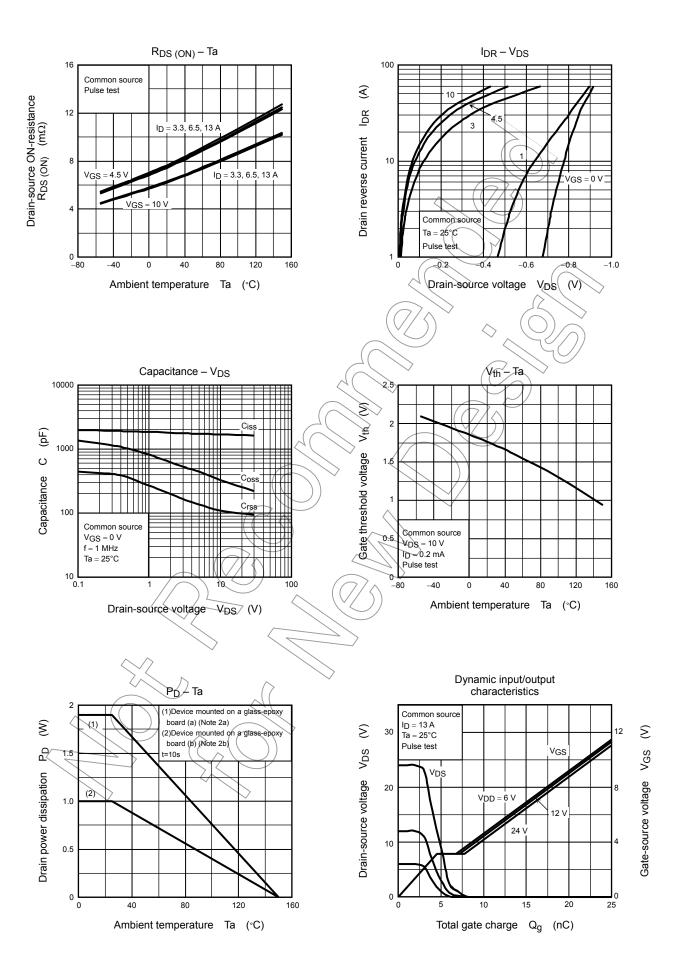
| Cha  | aracteristic  | Symbol               | Test Condition   | Min           | Тур. | Max        | Unit |
|--|---------------|----------------------|--|---------------|------|------------|------|
| Gate leakage curr                                  | rent          | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$                          | _             | _    | ±100       | nA   |
| Drain cutoff curre                                 | nt            | I <sub>DSS</sub>     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V                              | _             | _    | 10         | μΑ   |
| Drain-source breakdown voltage                     |               | V (BR) DSS           | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$                                | 30            | _    | _          | V    |
|  |               | V (BR) DSX           | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$                              | 15            | _    | _          | V    |
| Gate threshold vo                                  | ltage         | V <sub>th</sub>      | $V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA}$                              | 1.3           | ) >- | 2.3        | V    |
| Drain-source ON-resistance                         |               | Б                    | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 6.5 A                            | $\rightarrow$ | 7.7  | 11.1       | - mΩ |
|  |               | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.5 A                             | ))            | 6.4  | 9.7        |      |
| Forward transfer a                                 | admittance    | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 7 A                               | 24            | 48   | _          | S    |
| Input capacitance                                  |               | C <sub>iss</sub>     |  | _             | 1700 | 2200       |      |
| Reverse transfer                                   | capacitance   | C <sub>rss</sub>     | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$           | _             | 110  | 170        | pF   |
| Output capacitano                                  | ce            | C <sub>oss</sub>     |  |               | 330  | $\searrow$ |      |
| Gate resistance                                    |               | rg                   | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 5 MHz                   | -             | 2.3  | > 3.5      | Ω    |
| Switching time                                     | Rise time     | t <sub>r</sub>       | V <sub>GS</sub> 10 V I <sub>D</sub> = 6.5 A V <sub>OUT</sub>               |               | 5.5  | ) —        |      |
|  | Turn-on time  | t <sub>on</sub>      |  | 7             | 15   | _          | ne   |
|  | Fall time     | t <sub>f</sub>       | B = 2.   |               | 8.6  | _          | ns   |
|  | Turn-off time | t <sub>off</sub>     | V <sub>DD</sub> ≈ 15 V<br>Duty ≤ 1%, t <sub>w</sub> ≠ 10 μs                | _             | 39   | _          |      |
| Total gate charge<br>(gate-source plus gate-drain) |               | Qg                   | $V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 13 \text{ A}$ | _             | 24   | _          |      |
|  |               |                      | $V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 13 \text{ A}$  | _             | 12   | _          |      |
| Gate-source char                                   | ge 1 /        | Q <sub>ĝs1</sub>     |  | _             | 4.6  | _          | nC   |
| Gate-drain ("miller") charge                       |               | Qgd                  | $V_{DD} \approx 24 V$ , $V_{GS} = 10 V$ , $I_{D} = 13 A$                   | _             | 3.2  | _          |      |
| Gate switch charg                                  | ge (7)        | Q <sub>SW</sub>      |  | _             | 5.1  | _          |      |

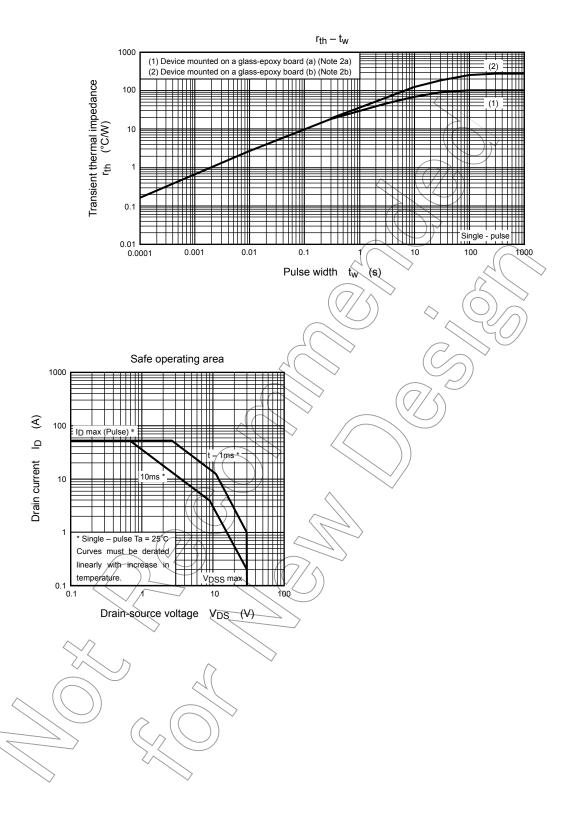
# Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                      | Symbol Test Condition  | Min | Тур. | Max  | Unit |
|--------------------------------------|--|-----|------|------|------|
| Drain reverse current Pulse (Note 1) | I <sub>DRP</sub> —   | _   | _    | 52   | Α    |
| Forward voltage (diode)              | V <sub>DSF</sub> I <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V | _   | _    | -1.2 | V    |



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